Single, Dual, Quad Low-Voltage, Rail-to-Rail Operational Amplifiers

LMV321, NCV321, LMV358, LMV324

The LMV321, LMV321I, NCV321, LMV358/LMV358I and LMV324 are CMOS single, dual, and quad low voltage operational amplifiers with rail−to−rail output swing. These amplifiers are a cost−effective solution for applications where low power consumption and space saving packages are critical. Specification tables are provided for operation from power supply voltages at 2.7 V and 5 V. Rail−to−Rail operation provides improved signal−to−noise preformance. Ultra low quiescent current makes this series of amplifiers ideal for portable, battery operated equipment. The common mode input range includes ground making the device useful for low−side current−shunt measurements. The ultra small packages allow for placement on the PCB in close proximity to the signal source thereby reducing noise pickup.

Features

- Operation from 2.7 V to 5.0 V Single−Sided Power Supply
- LMV321 Single Available in Ultra Small 5 Pin SC70 Package
- No Output Crossover Distortion
- Rail−to−Rail Output
- Low Quiescent Current: LMV358 Dual − 220 μA, Max per Channel
- No Output Phase−Reversal from Overdriven Input
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Notebook Computers and PDA's
- Portable Battery−Operated Instruments
- Active Filters

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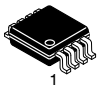
SC−70
CASE 419A

TSOP−5
CASE 483

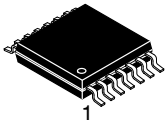


Micro8
CASE 846A

SOIC−8
CASE 751

UDFN8
CASE 517AJ

SOIC−14
CASE 751A



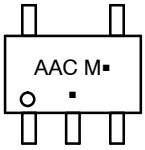
TSSOP−14
CASE 948G

ORDERING AND MARKING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

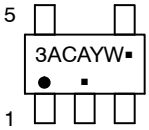
MARKING DIAGRAMS

SC−70



AAC = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

TSOP−5

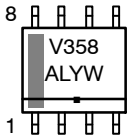


3AC = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

Micro8

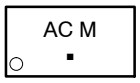
V358 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

SOIC−8



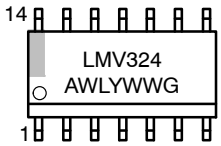
V358 = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

UDFN8



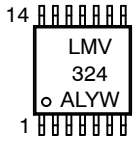
AC = Specific Device Code
M = Date Code
▪ = Pb−Free Package

SOIC−14



LMV324 = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

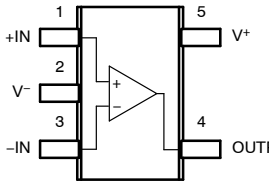
TSSOP−14



LMV324 = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

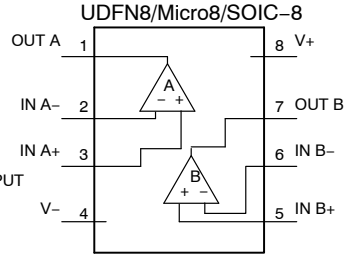
PIN CONNECTIONS

SC70−5/TSOP−5



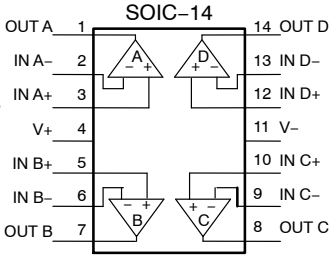
(Top View)

UDFN8/Micro8/SOIC−8



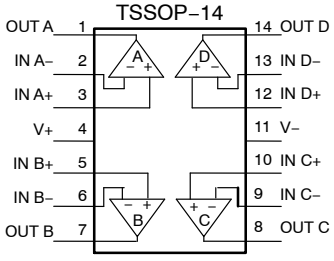
(Top View)

SOIC−14



(Top View)

TSSOP−14



(Top View)

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V_S	Supply Voltage (Operating Range V_S = 2.7 V to 5.5 V)	5.5	V
V_{IDR}	Input Differential Voltage	± Supply Voltage	V
V_{ICR}	Input Common Mode Voltage Range	−0.5 to (V+) + 0.5	V
	Maximum Input Current	10	mA
t_{So}	Output Short Circuit (Note 1)	Continuous	
T_J	Maximum Junction Temperature	150	°C
T_A	Operating Ambient Temperature Range LMV321, LMV358, LMV324 LMV321I, LMV358I NCV321 (Note 2)	 −40 to 85 −40 to 125 −40 to 125	 °C °C °C
θ_{JA}	Thermal Resistance:		°C/W
	SC−70	280	
	Micro8	238	
	TSOP−5	333	
	UDFN8 (1.2 mm x 1.8 mm x 0.5 mm)	350	
	SOIC−8	212	
	SOIC−14	156	
	TSSOP−14	190	
T_{stg}	Storage Temperature	−65 to 150	°C
	Mounting Temperature (Infrared or Convection −20 sec)	260	°C
V_{ESD}	ESD Tolerance (Note 3) LMV321, LMV321I, NCV321 Machine Model Human Body Model LMV358/358I/324 Machine Model Human Body Mode	 100 1000 100 2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Continuous short−circuit operation to ground at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of 45 mA over long term may adversely affect reliability. Shorting output to either V+ or V− will adversely affect reliability.
2. NCV prefix is qualified for automotive usage.
3. Human Body Model, applicable std. MIL−STD−883, Method 3015.7
   Machine Model, applicable std. JESD22−A115−A (ESD MM std. of JEDEC)
   Field−Induced Charge−Device Model, applicable std. JESD22−C101−C (ESD FICDM std. of JEDEC).

2.7 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V^+ = 2.7 V, R_L = 1 MΩ, V^- = 0 V, V_O = V+/2)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Input Offset Voltage	V_{IO}	$T_A = T_{Low}$ to T_{High} (Note 4)		1.7	9	mV
Input Offset Voltage Average Drift	ICV_{OS}	$T_A = T_{Low}$ to T_{High} (Note 4)		5		μV/°C
Input Bias Current	I_B	$T_A = T_{Low}$ to T_{High} (Note 4)		<1		nA
Input Offset Current	I_{IO}	$T_A = T_{Low}$ to T_{High} (Note 4)		<1		nA
Common Mode Rejection Ratio	CMRR	0 V ≤ V_{CM} ≤ 1.7 V	50	63		dB
Power Supply Rejection Ratio	PSRR	2.7 V ≤ V+ ≤ 5 V, V_O = 1 V	50	60		dB
Input Common−Mode Voltage Range	V_{CM}	For CMRR ≥ 50 dB	0 to 1.7	−0.2 to 1.9		V
Output Swing	V_{OH}	R_L = 10 kΩ to 1.35 V	V_{CC} − 100	V_{CC} − 10		mV
	V_{OL}	R_L = 10 kΩ to 1.35 V (Note 5)		60	180	mV
Supply Current LMV321, NCV321 LMV358/LMV358I (Both Amplifiers) LMV324 (4 Amplifiers)	I_{CC}			80 140 260	185 340 680	μA

2.7 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V^+ = 2.7 V, R_L = 1 MΩ, V^- = 0 V, V_O = V+/2)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gain Bandwidth Product	GBWP	C_L = 200 pF		1		MHz
Phase Margin	Θ_m			60		°
Gain Margin	G_m			10		dB
Input−Referred Voltage Noise	e_n	f = 50 kHz		50		nV/$\sqrt{Hz}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. For LMV321, LMV358, LMV324: T_A = −40°C to +85°C
   For LMV321I, LMV358I, NCV321: T_A = −40°C to +125°C.
5. Guaranteed by design and/or characterization.

5.0 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V^+ = 5.0 V, R_L = 1 MΩ, V^- = 0 V, V_O = V+/2)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Input Offset Voltage	V_{IO}	$T_A = T_{Low}$ to T_{High} (Note 6)		1.7	9	mV
Input Offset Voltage Average Drift	T_CV_{IO}	$T_A = T_{Low}$ to T_{High} (Note 6)		5		μV/°C
Input Bias Current (Note 7)	I_B	$T_A = T_{Low}$ to T_{High} (Note 6)		< 1		nA
Input Offset Current (Note 7)	I_{IO}	$T_A = T_{Low}$ to T_{High} (Note 6)		< 1		nA
Common Mode Rejection Ratio	CMRR	0 V ≤ V_{CM} ≤ 4 V	50	65		dB
Power Supply Rejection Ratio	PSRR	2.7 V ≤ V+ ≤ 5 V, V_O = 1 V, V_{CM} = 1 V	50	60		dB
Input Common−Mode Voltage Range	V_{CM}	For CMRR ≥ 50 dB	0 to 4	−0.2 to 4.2		V
Large Signal Voltage Gain (Note 7)	A_V	R_L = 2 kΩ	15	100		V/mV
		$T_A = T_{Low}$ to T_{High} (Note 6)	10			
Output Swing	V_{OH}	R_L = 2 kΩ to 2.5 V $T_A = T_{Low}$ to T_{High} (Note 6)	V_{CC} − 300 V_{CC} − 400	V_{CC} − 40		mV
	V_{OL}	R_L = 2 kΩ to 2.5 V (Note 7) $T_A = T_{Low}$ to T_{High} (Note 6)		120	300 400	mV
	V_{OH}	R_L = 10 kΩ to 2.5 V (Note 7) $T_A = T_{Low}$ to T_{High} (Note 6)	V_{CC} − 100 V_{CC} − 200			mV
	V_{OL}	R_L = 10 kΩ to 2.5 V $T_A = T_{Low}$ to T_{High} (Note 6)		65	180 280	mV
Output Short Circuit Current	I_O	Sourcing = V_O = 0 V (Note 7) Sinking = V_O = 5 V (Note 7)	10 10	60 160		mA
Supply Current	I_{CC}	LMV321 $T_A = T_{Low}$ to T_{High} (Note 6)		130	250 350	μA
		NCV321 $T_A = T_{Low}$ to T_{High} (Note 6)		130	250 350	
		LMV358/358I Both Amplifiers $T_A = T_{Low}$ to T_{High} (Note 6)		210	440 615	
		LMV324 All Four Amplifiers $T_A = T_{Low}$ to T_{High} (Note 6)		410	830 1160	

5.0 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V^+ = 5.0 V, R_L = 1 MΩ, V^- = 0 V, V_O = V+/2)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Slew Rate	S_R			1		V/μs
Gain Bandwidth Product	GBWP	C_L = 200 pF		1		MHz
Phase Margin	Θ_m			60		°
Gain Margin	G_m			10		dB
Input−Referred Voltage Noise	e_n	f = 50 kHz		50		nV/$\sqrt{Hz}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. For LMV321, LMV358, LMV324: T_A = −40°C to +85°C
   For LMV321I, LMV358I, NCV321: T_A = −40°C to +125°C.
7. Guaranteed by design and/or characterization.

TYPICAL CHARACTERISTICS

(T_A = 25°C and V_S = 5 V unless otherwise specified)

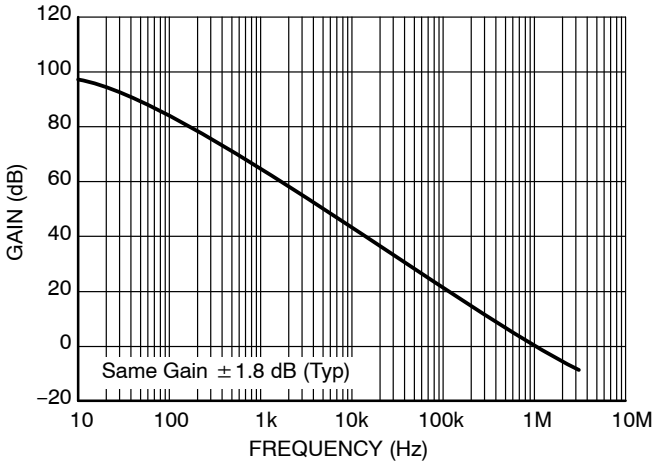


Figure 1. Open Loop Frequency Response (R_L = 2 kΩ, T_A = 25°C, V_S = 5 V)

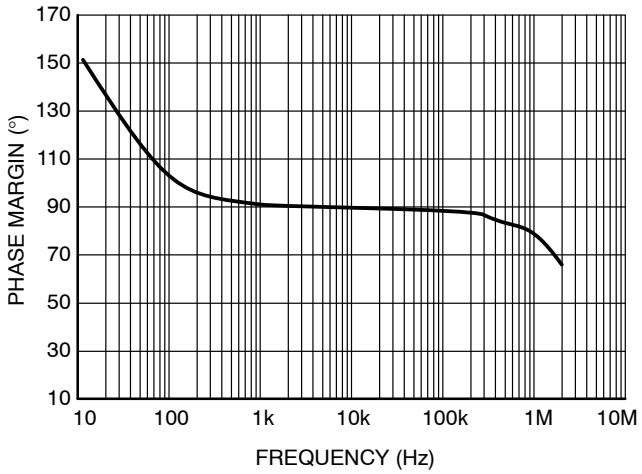


Figure 2. Open Loop Phase Margin (R_L = 2 kΩ, T_A = 25°C, V_S = 5 V)

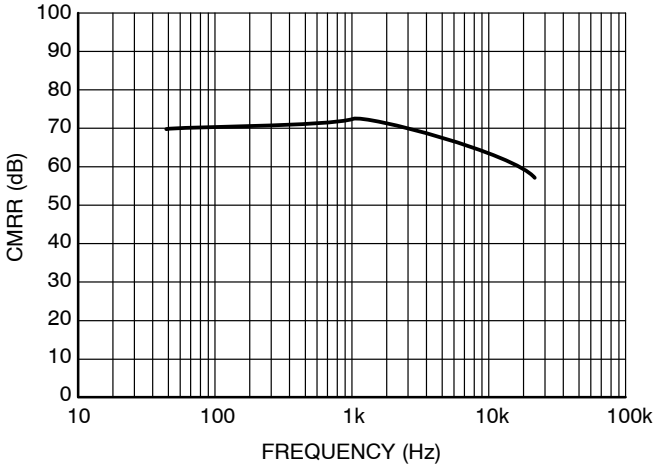


Figure 3. CMRR vs. Frequency (R_L = 5 kΩ, V_S = 5 V)

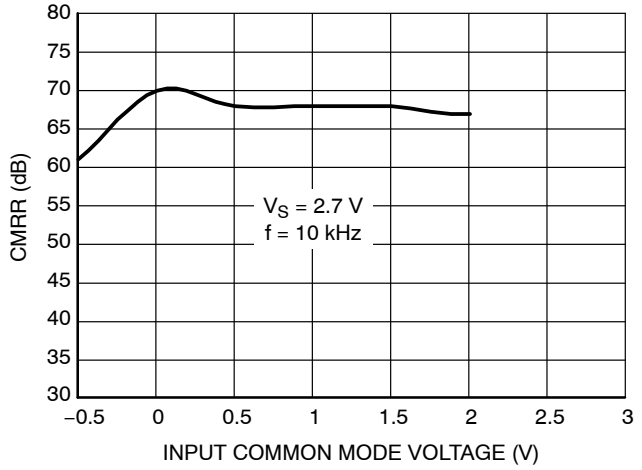


Figure 4. CMRR vs. Input Common Mode Voltage

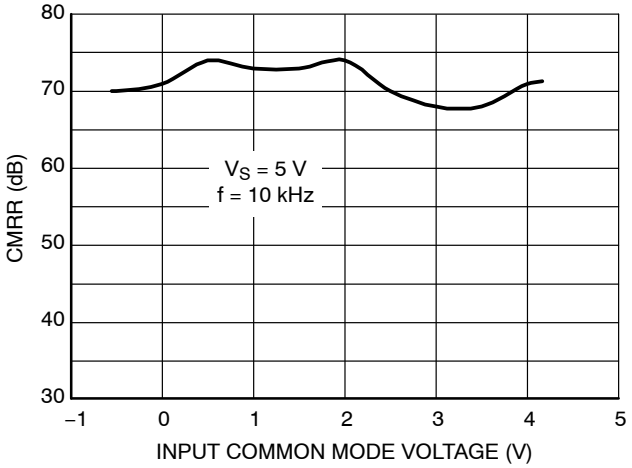


Figure 5. CMRR vs. Input Common Mode Voltage

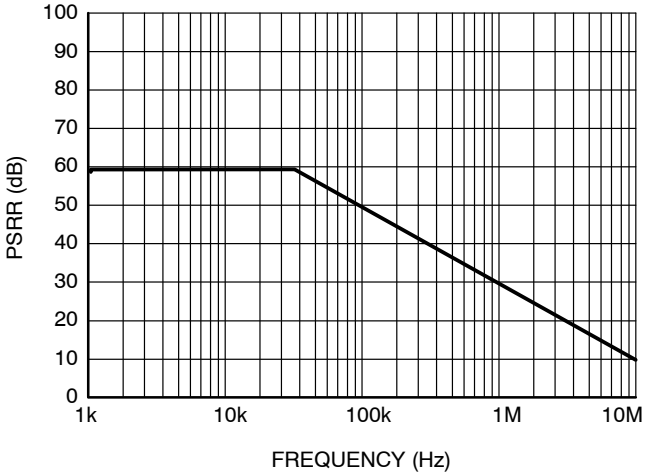


Figure 6. PSRR vs. Frequency (R_L = 5 kΩ, V_S = 2.7 V, +PSRR)

TYPICAL CHARACTERISTICS

(T_A = 25°C and V_S = 5 V unless otherwise specified)

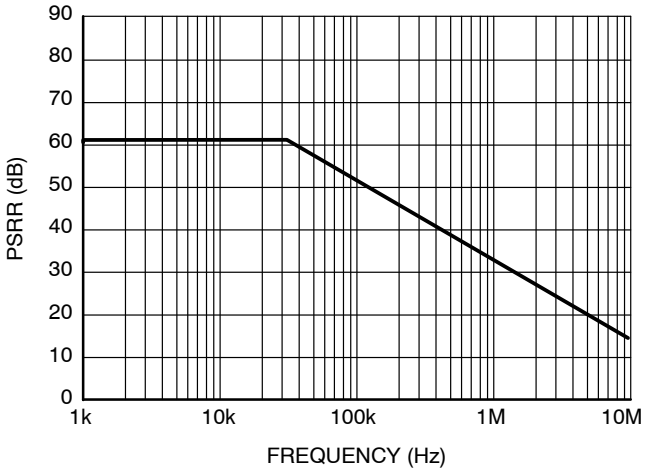


Figure 7. PSRR vs. Frequency (R_L = 5 kΩ, V_S = 2.7 V, −PSRR)

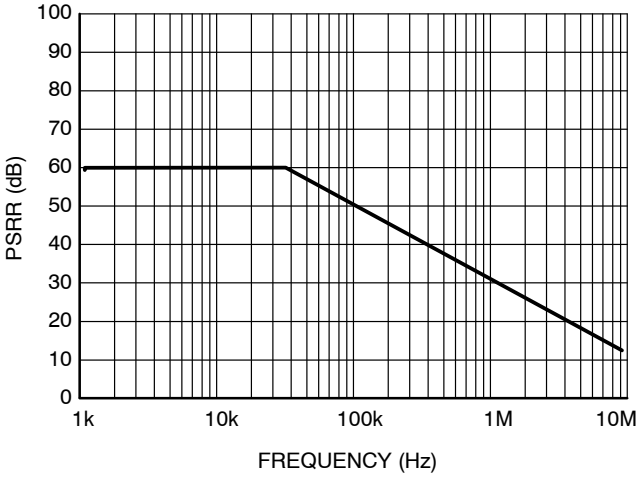


Figure 8. PSRR vs. Frequency (R_L = 5 kΩ, V_S = 5 V, +PSRR)

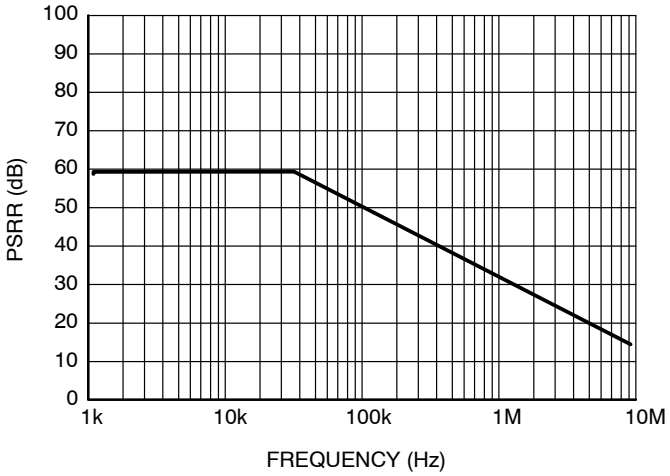


Figure 9. PSRR vs. Frequency (R_L = 5 kΩ, V_S = 5 V, −PSRR)

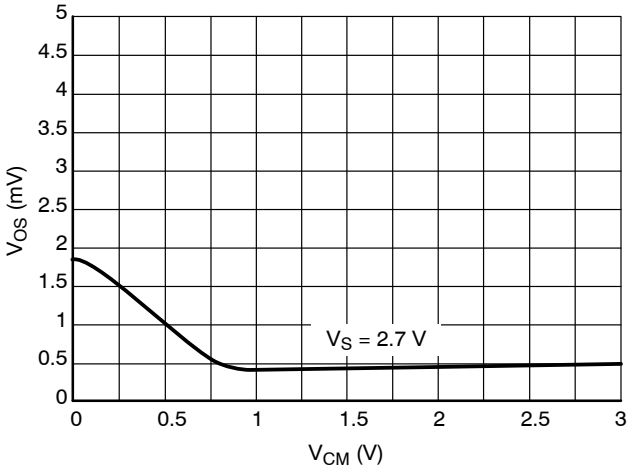


Figure 10. V_{OS} vs CMR

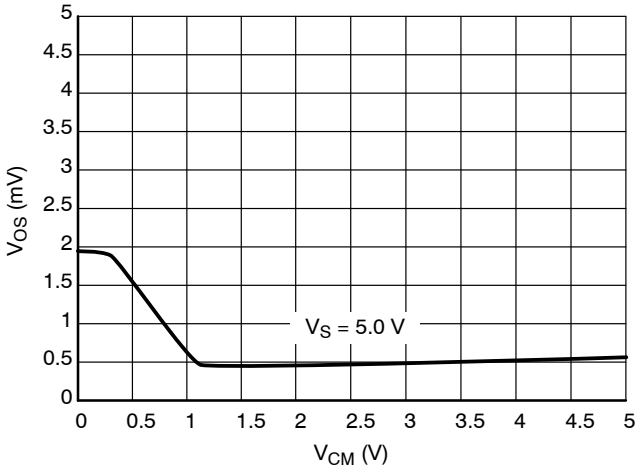


Figure 11. V_{OS} vs CMR

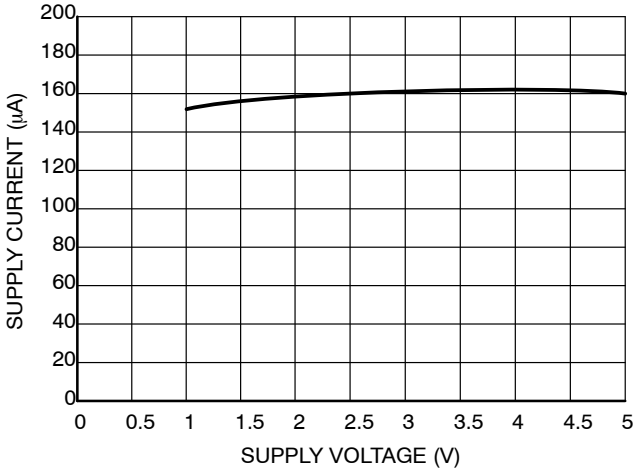


Figure 12. Supply Current vs. Supply Voltage

TYPICAL CHARACTERISTICS

(T_A = 25°C and V_S = 5 V unless otherwise specified)

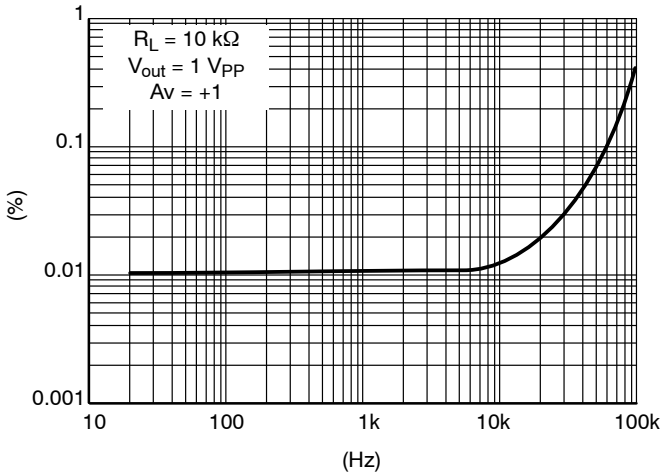


Figure 13. THD+N vs Frequency

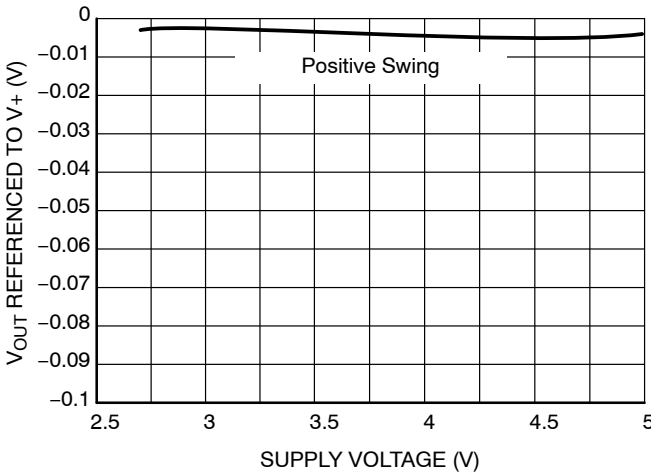


Figure 14. Output Voltage Swing vs Supply Voltage (R_L = 10k)

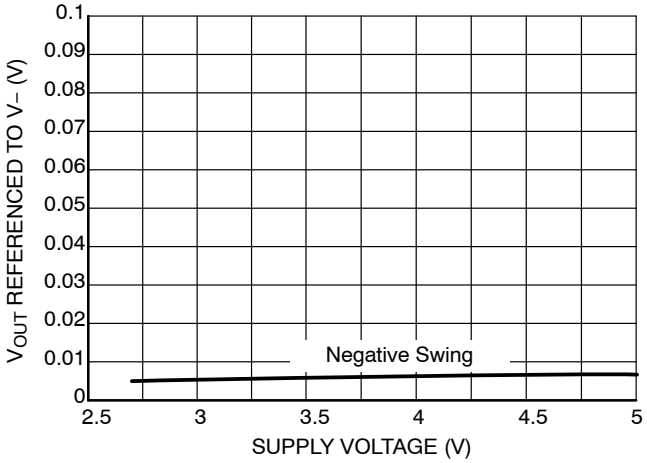


Figure 15. Output Voltage Swing vs Supply Voltage (R_L = 10k)

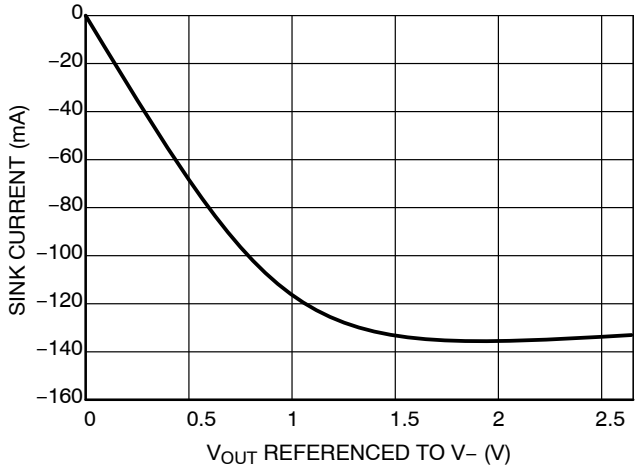


Figure 16. Sink Current vs. Output Voltage V_S = 2.7 V

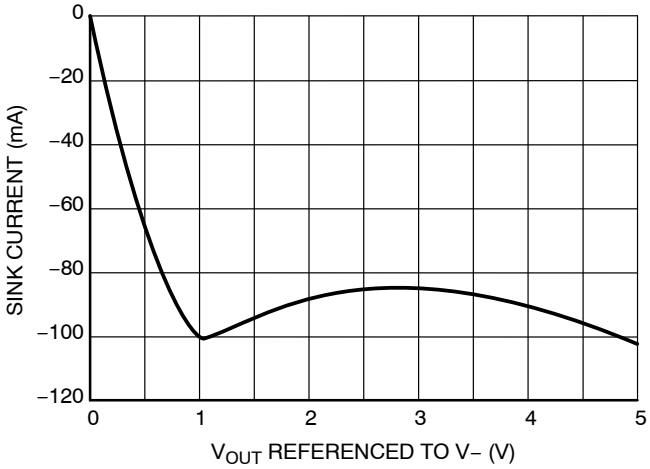


Figure 17. Sink Current vs. Output Voltage V_S = 5.0 V

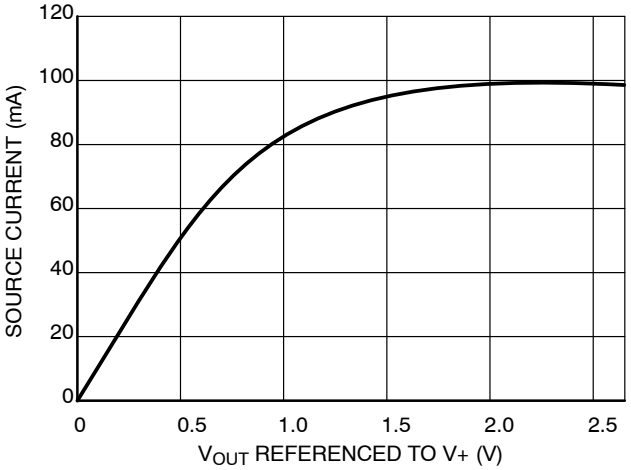


Figure 18. Source Current vs. Output Voltage V_S = 2.7 V

TYPICAL CHARACTERISTICS

(T_A = 25°C and V_S = 5 V unless otherwise specified)

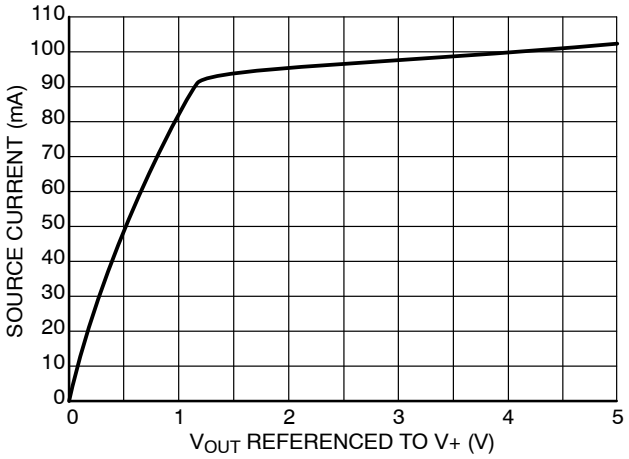


Figure 19. Source Current vs. Output Voltage
V_S = 5.0 V

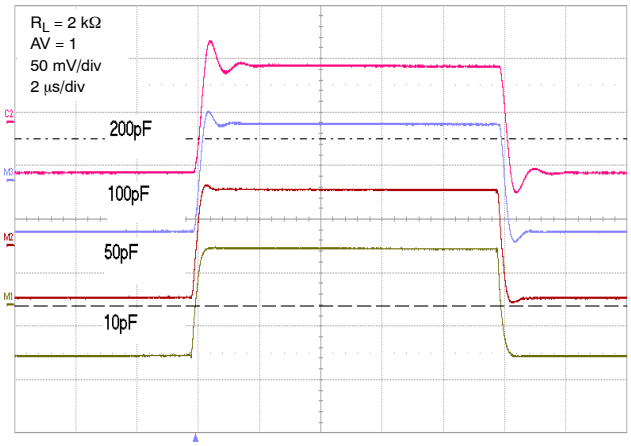


Figure 20. Settling Time vs. Capacitive Load

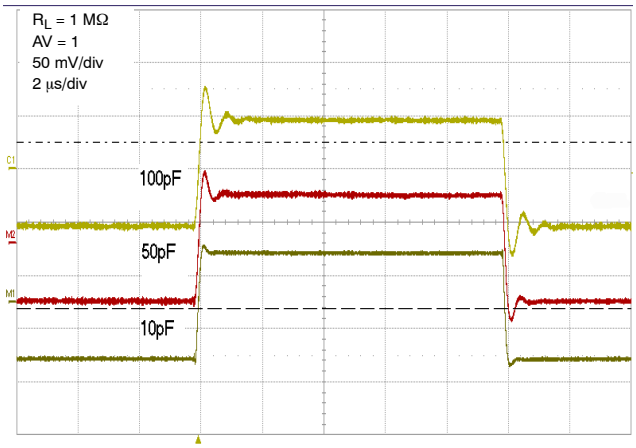


Figure 21. Settling Time vs. Capacitive Load

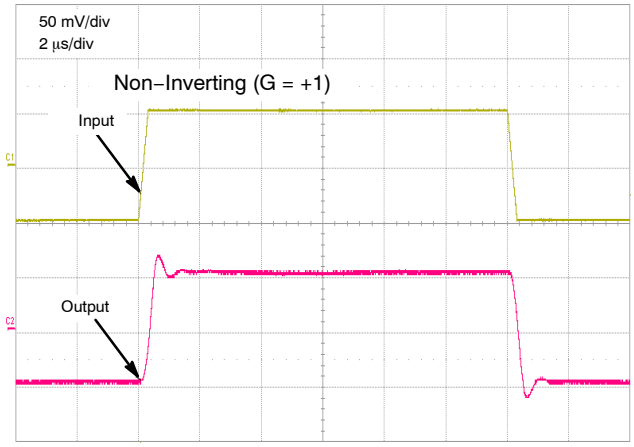


Figure 22. Step Response − Small Signal

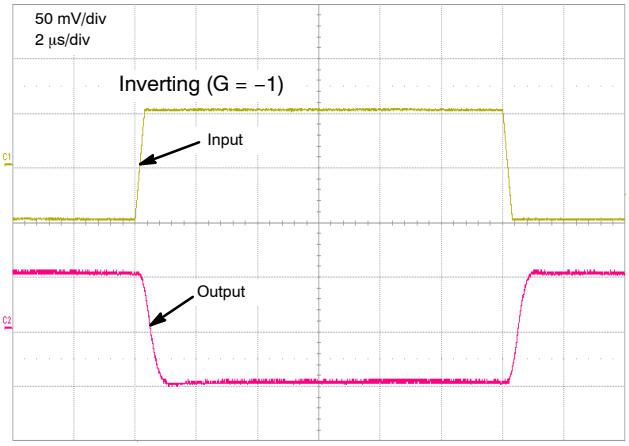


Figure 23. Step Response − Small Signal

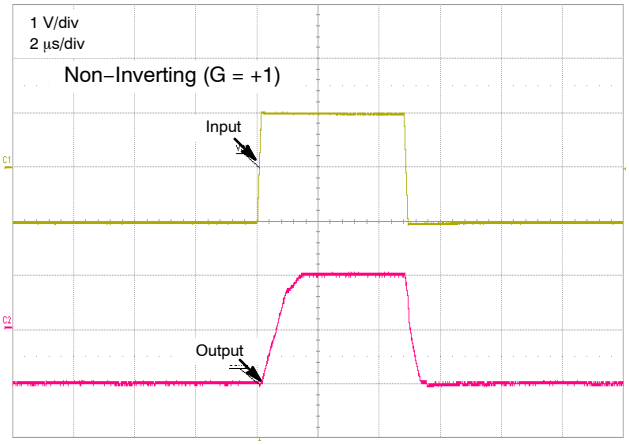


Figure 24. Step Response − Large Signal

TYPICAL CHARACTERISTICS

(T_A = 25°C and V_S = 5 V unless otherwise specified)

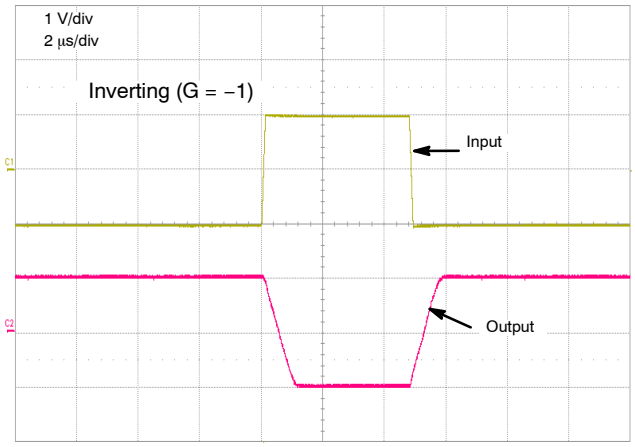


Figure 25. Step Response − Large Signal

APPLICATIONS

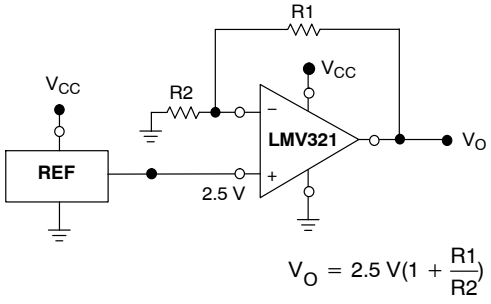


Figure 26. Voltage Reference

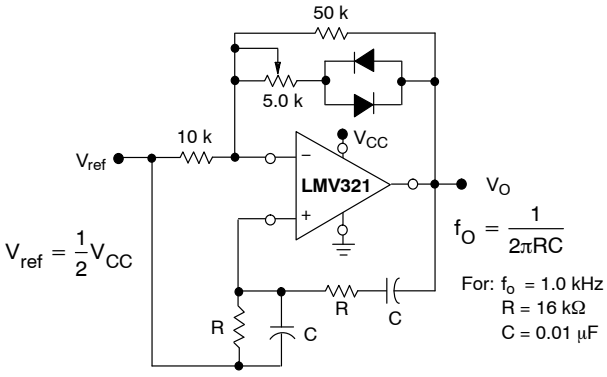
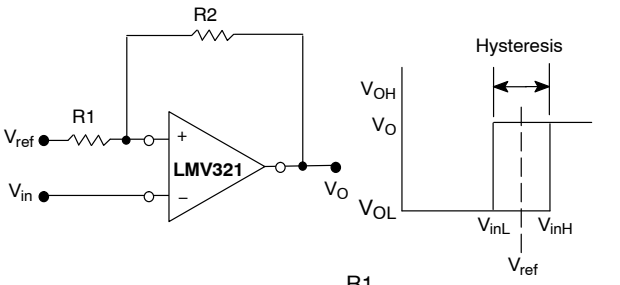


Figure 27. Wien Bridge Oscillator

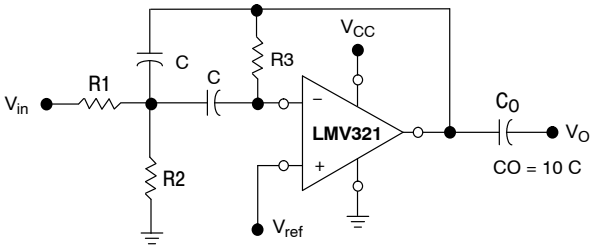


$$V_{in}L = \frac{R1}{R1 + R2}\ (V_{OL} - V_{ref}) + V_{ref}$$

$$V_{in}H = \frac{R1}{R1 + R2}\ (V_{OH} - V_{ref}) + V_{ref}$$

$$H = \frac{R1}{R1 + R2}\ (V_{OH} - V_{OL})$$

Figure 28. Comparator with Hysteresis



Given: f_o = center frequency
$A(f_o)$ = gain at center frequency

Choose value f_o, C

Then : $R3 = \frac{Q}{\pi f_O C}$

$$R1 = \frac{R3}{2\ A(f_O)}$$

$$R2 = \frac{R1\ R3}{4Q^2\ R1 - R3}$$

For less than 10% error from operational amplifier, $((Q_O\ f_O)/BW) < 0.1$ where f_o and BW are expressed in Hz. If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

Figure 29. Multiple Feedback Bandpass Filter

ORDERING INFORMATION

Order Number	Number of Channels	Specific Device Marking	Package Type	Shipping†
LMV321SQ3T2G	Single	AAC	SC−70 (Pb−Free)	3000 / Tape & Reel
LMV321SN3T1G	Single	3AC	TSOP−5 (Pb−Free)	3000 / Tape & Reel
LMV321ISN3T1G	Single	3AC	TSOP−5 (Pb−Free)	3000 / Tape & Reel
NCV321SN3T1G*	Single	3AC	TSOP−5 (Pb−Free)	3000 / Tape & Reel
LMV358DMR2G	Dual	V358	Micro8 (Pb−Free)	4000 / Tape & Reel
LMV358MUTAG	Dual	AC	UDFN8 (Pb−Free)	3000 / Tape & Reel
LMV358DR2G	Dual	V358	SOIC−8 (Pb−Free)	2500 / Tape & Reel
LMV358IDR2G	Dual	V358	SOIC−8 (Pb−Free)	2500 / Tape & Reel
LMV324DR2G	Quad	LMV324	SOIC−14 (Pb−Free)	2500 / Tape & Reel
LMV324DTBR2G	Quad	LMV 324	TSSOP−14 (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

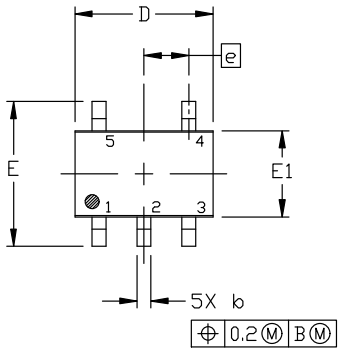
*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

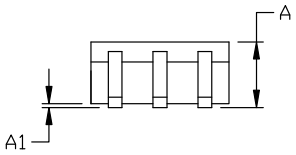
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

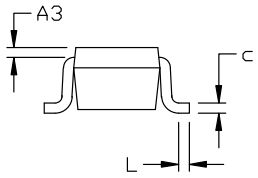
SCALE 2:1

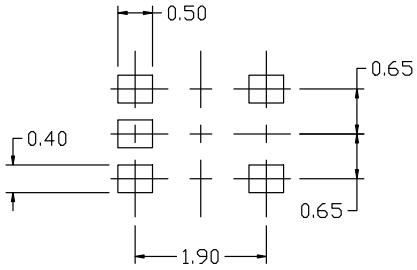
SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE M

DATE 11 APR 2023









RECOMMENDED
MOUNTING FOOTPRINT

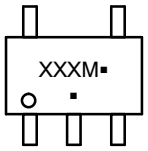
* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.80	0.95	1.10
A1	---	---	0.10
A3	0.20 REF		
b	0.10	0.20	0.30
c	0.10	---	0.25
D	1.80	2.00	2.20
E	2.00	2.10	2.20
E1	1.15	1.25	1.35
e	0.65 BSC		
L	0.10	0.15	0.30

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR
5. COLLECTOR 2/BASE 1

STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

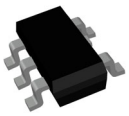
STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

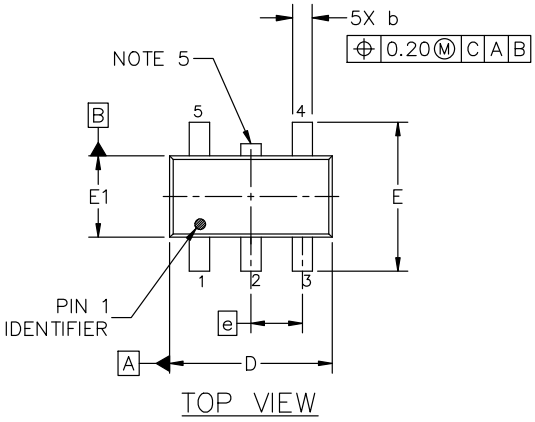
DOCUMENT NUMBER:	98ASB42984B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SC−88A (SC−70−5/SOT−353)	PAGE 1 OF 1

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

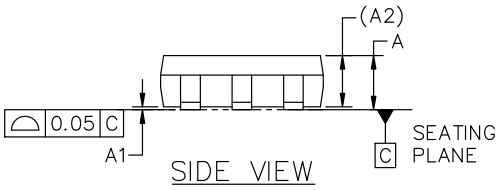


TSOP−5 3.00x1.50x0.95, 0.95P
CASE 483
ISSUE P

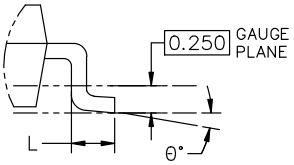
DATE 01 APR 2024



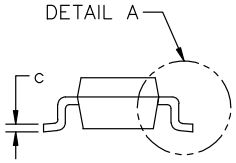
TOP VIEW



SIDE VIEW



DETAIL "A"
SCALE 2:1

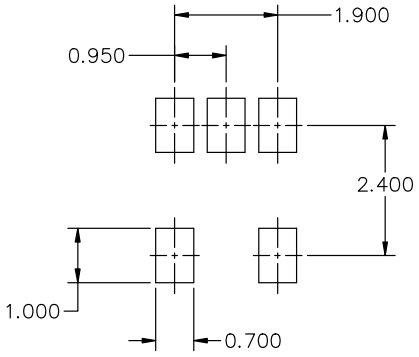


END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES).
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

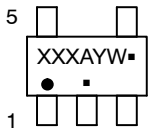
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.900	1.000	1.100
A1	0.010	0.055	0.100
A2		0.950 REF.	
b	0.250	0.375	0.500
c	0.100	0.180	0.260
D	2.850	3.000	3.150
E	2.500	2.750	3.000
E1	1.350	1.500	1.650
e		0.950 BSC	
L	0.200	0.400	0.600
θ	0°	5°	10°



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

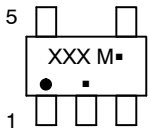
GENERIC
MARKING DIAGRAM*



Analog

XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)



Discrete/Logic

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

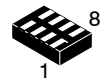
DOCUMENT NUMBER:	**98ARB18753C**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**TSOP−5 3.00x1.50x0.95, 0.95P**	**PAGE 1 OF 1**

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

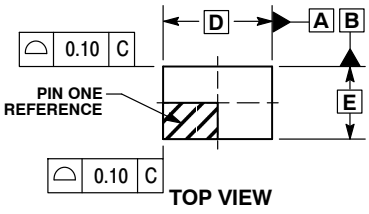
ON Semiconductor®

UDFN8 1.8x1.2, 0.4P
CASE 517AJ−01
ISSUE O

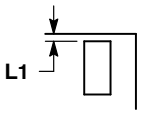
DATE 08 NOV 2006



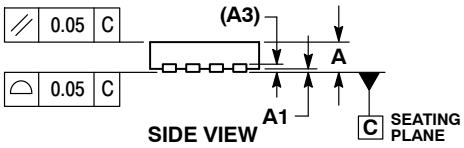
SCALE 4:1



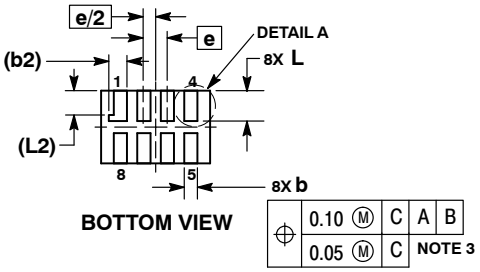
TOP VIEW



DETAIL A
NOTE 5



SIDE VIEW



BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL TIP.
4. MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH MAY NOT EXCEED 0.03 ONTO BOTTOM SURFACE OF TERMINALS.
5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

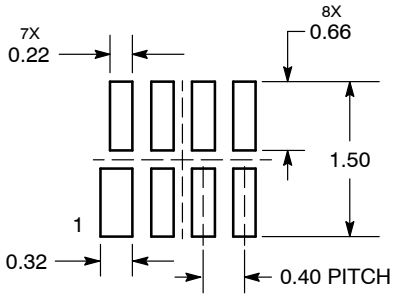
	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.127 REF	
b	0.15	0.25
b2	0.30 REF	
D	1.80 BSC	
E	1.20 BSC	
e	0.40 BSC	
L	0.45	0.55
L1	0.00	0.03
L2	0.40 REF	

GENERIC MARKING DIAGRAM*

XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

MOUNTING FOOTPRINT SOLDERMASK DEFINED



DIMENSIONS: MILLIMETERS

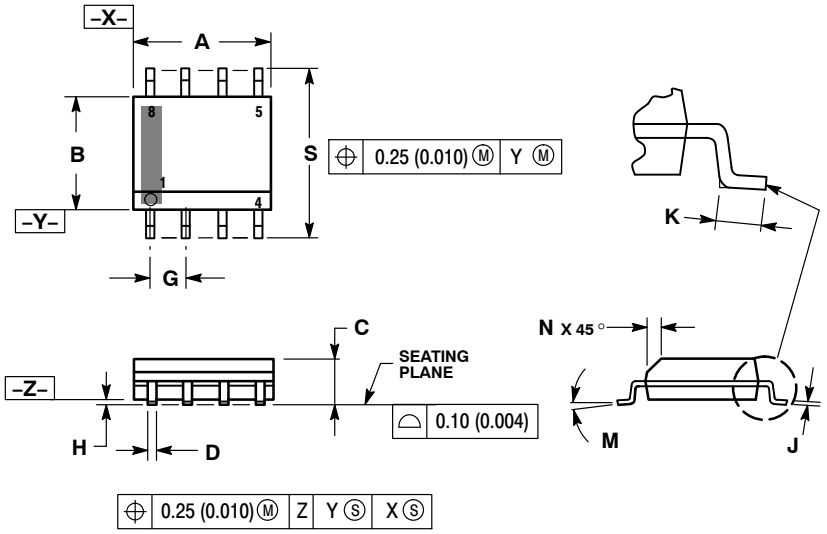
DOCUMENT NUMBER:	**98AON23417D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**UDFN8 1.8X1.2, 0.4P**		**PAGE 1 OF 1**

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SCALE 1:1

SOIC−8 NB
CASE 751−07
ISSUE AK

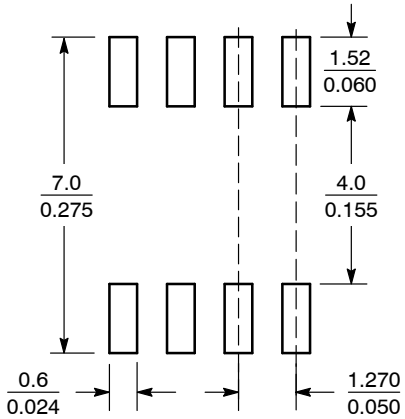
DATE 16 FEB 2011



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

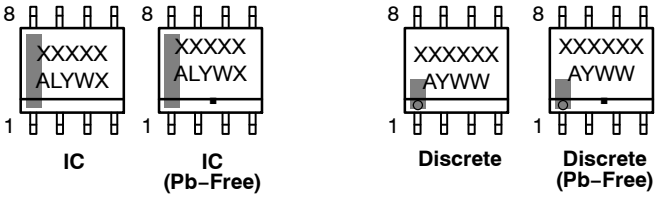
SOLDERING FOOTPRINT*



SCALE 6:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



IC | IC (Pb−Free) | Discrete | Discrete (Pb−Free)

XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42564B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**SOIC−8 NB**	**PAGE 1 OF 2**

SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

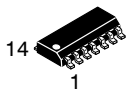
STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

DOCUMENT NUMBER:	**98ASB42564B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SOIC−8 NB**		**PAGE 2 OF 2**

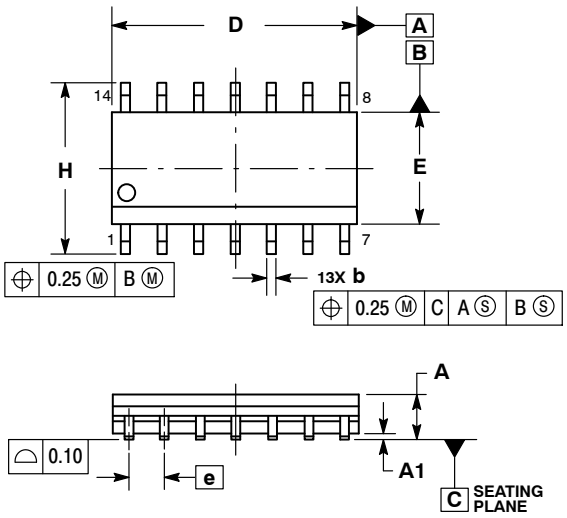
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

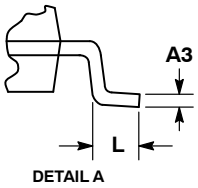


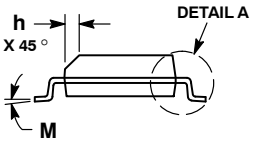
SCALE 1:1

SOIC−14 NB
CASE 751A−03
ISSUE L

DATE 03 FEB 2016



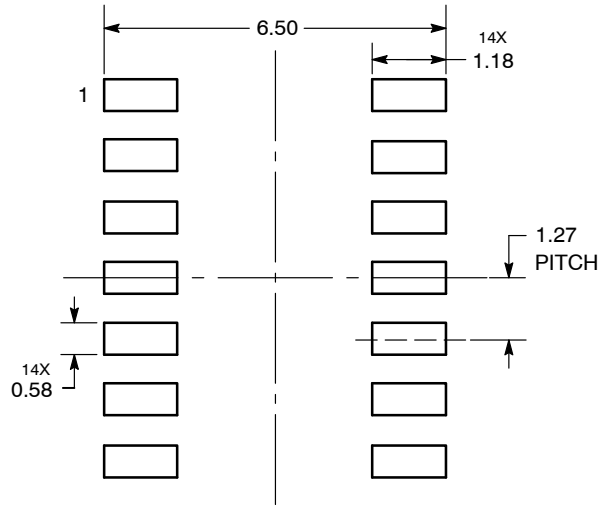




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

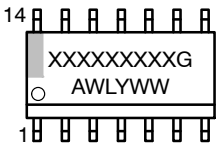
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42565B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOIC−14 NB**		**PAGE 1 OF 2**

SOIC−14
CASE 751A−03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

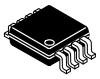
STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

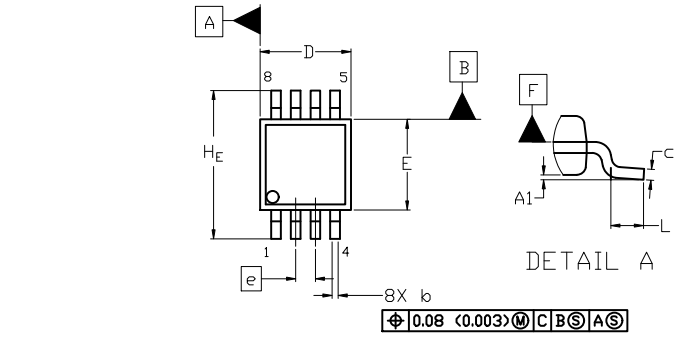
ON Semiconductor®

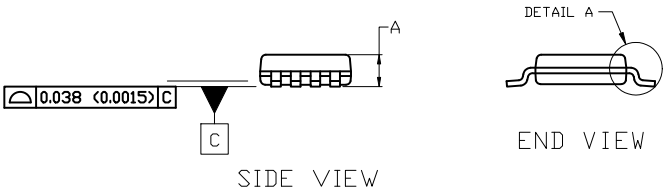


SCALE 2:1

Micro8
CASE 846A−02
ISSUE K

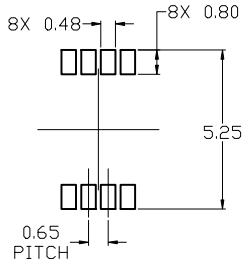
DATE 16 JUL 2020





NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

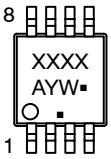


RECOMMENDED
MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.65 BSC		
H_E	4.75	4.90	5.05
L	0.40	0.55	0.70

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 2:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 3:
PIN 1. N-SOURCE
2. N-GATE
3. P-SOURCE
4. P-GATE
5. P-DRAIN
6. P-DRAIN
7. N-DRAIN
8. N-DRAIN

DOCUMENT NUMBER:	**98ASB14087C**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**MICRO8**	**PAGE 1 OF 1**

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